

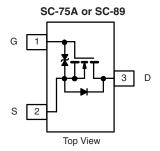
HALOGEN

FREE



N-Channel 1.8 V (G-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (mA)		
	0.70 at V _{GS} = 4.5 V	600		
20	0.85 at V _{GS} = 2.5 V	500		
	1.25 at V _{GS} = 1.8 V	350		



ORDERING INFORMATION				
Part Number	Package	Marking Code		
Si1012R-T1-GE3 (Lead (Pb)-free and Halogen-free)	SC-75A (SOT-416)	С		
Si1012X-T1-GE3 (Lead (Pb)-free and Halogen-free)	SC-89 (SOT-490)	А		

FEATURES

TrenchFET® Power MOSFET: 1.8 V Rated

Gate-Source ESD Protected: 2000 V

High-Side Switching

Low On-Resistance: 0.7 Ω

Low Threshold: 0.8 V (typ.)

Fast Switching Speed: 10 ns

Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- **Battery Operated Systems**
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- **High-Speed Circuits**
- Low Battery Voltage Operation

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	5 s	Steady State	Unit		
Drain-Source Voltage	V _{DS}	20		V		
Gate-Source Voltage		V _{GS}	± 6			
0 D 0 (T)	T _A = 25 °C		600	500		
Continuous Drain Current (T _J = 150 °C) ^b	T _A = 85 °C	I _D	400	350		
Pulsed Drain Current ^a		I _{DM}	1000		mA	
Continuous Source Current (Diode Conduction) ^b		I _S	275	250	ı	
	T _A = 25 °C		175	150	mW	
Maximum Power Dissipation ^b for SC-75	T _A = 85 °C		90	80		
	T _A = 25 °C	P _D	275	250		
Maximum Power Dissipation ^b for SC-89	T _A = 85 °C		160	140		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000		V	

- a. Pulse width limited by maximum junction temperature.
- b. Surface mounted on FR4 board.

Si1012R, Si1012X

Vishay Siliconix



SPECIFICATIONS (T _A = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.45		0.9	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$		± 0.5	± 1	μΑ	
Zara Cata Valtaria Duais Comment	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V		0.3	100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 4.5 V	700			mA	
		$V_{GS} = 4.5 \text{ V}, I_D = 600 \text{ mA}$	0.41		0.70		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 500 \text{ mA}$		0.53	0.85		
		$V_{GS} = 1.8 \text{ V}, I_D = 350 \text{ mA}$		0.70	1.25		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 400 mA		1		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 150 mA, V _{GS} = 0 V		0.8	1.2	V	
Dynamic ^b	'		•		•		
Total Gate Charge	Q_g			750			
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 250 \text{ mA}$		75		рC	
Gate-Drain Charge	Q_{gd}			225		1	
Turn-On Delay Time	t _{d(on)}			5			
Rise Time	t _r	V_{DD} = 10 V, R_L = 47 Ω		5			
Turn-Off Delay Time	t _{d(off)}	$\rm I_D\cong 200$ mA, $\rm V_{GEN}=4.5$ V, $\rm R_g=10~\Omega$		25		ns	
Fall Time	t _f			11			

Notes:

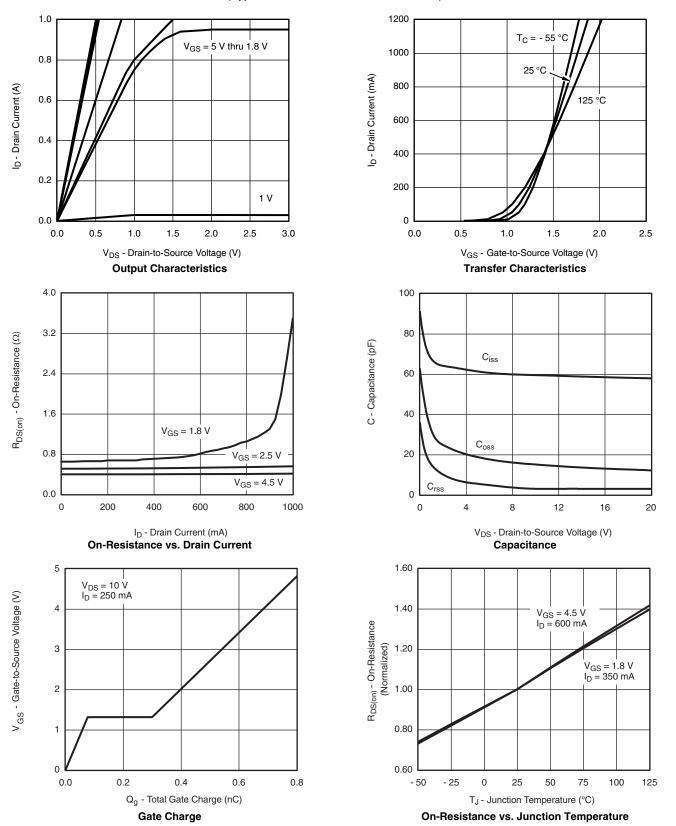
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

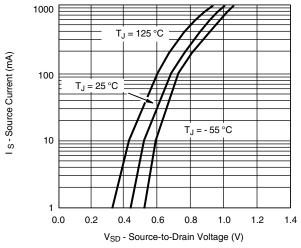


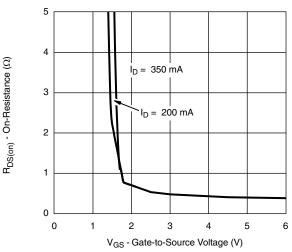
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



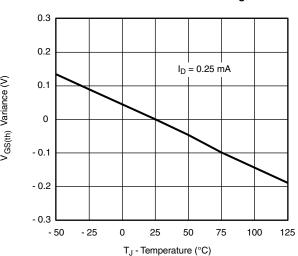
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

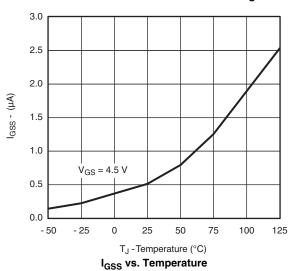




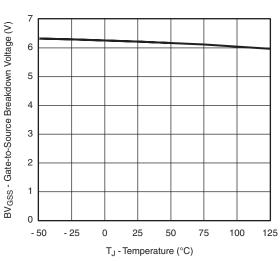
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



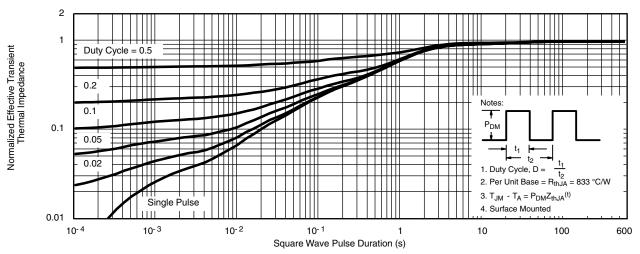
Threshold Voltage Variance vs. Temperature



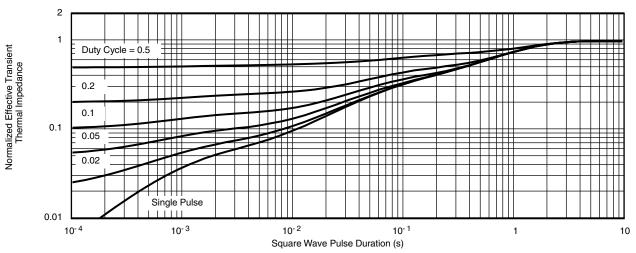
BV_{GSS} vs. Temperature



TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient (SC-75A)

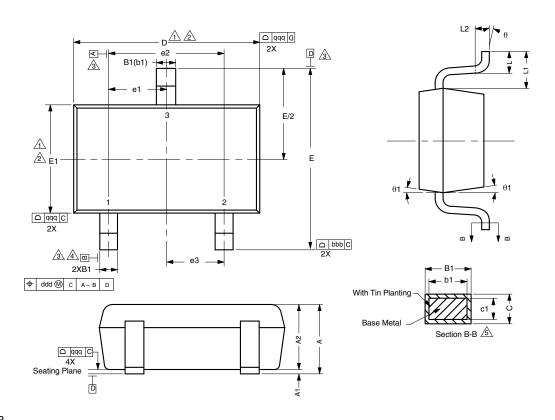


Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71166.



SC-75A: 3 Leads



DWG: 5868

Notes

Dimensions in millimeters will govern.

- Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
- Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
- ②Datums A, B and D to be determined 0.10 mm from the lead tip.

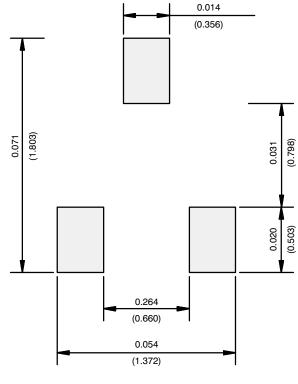
 4\text{Terminal positions are shown for reference only.}
- These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES
aaa	0.10
bbb	0.10
ccc	0.10
ddd	0.10

DIM.	N	NOTE		
Dilvi.	MIN.	NOM.	MAX.	NOTE
А	-	-	0.80	
A1	0.00	-	0.10	
A2	0.65	0.70	0.80	
B1	0.19	-	0.24	5
b1	0.17	-	0.21	
С	0.13	-	0.15	5
c1	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
Е	1.50	1.60	1.70	
E1	0.66	0.76	0.86	1, 2
e1	0.50 BSC			
e2	1.00 BSC			
e3	0.50 BSC			
L	0.15	0.205	0.30	
L1	0.40 ref.			
L2	0.15 BSC			
q	0°	-	8°	
q1	4°	-	10°	



RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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